Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Thermal characteristics[2]						
Thermal resistance, junction - case	R_{thJC}	-	-	-	1.2	K/W
SMD version, device on PCB	R_{thJA}	minimal footprint	-	-	62	
		6 cm^2 cooling area[3]	-	-	40	
Electrical characteristics, at T_j=25 °C, unless otherwise specified						
Static characteristics						
Drain-source breakdown voltage	$V_{(BR)DSS}$	V_{GS}=0V, I_D= -1mA	-40	-	-	V
Gate threshold voltage	$V_{GS(th)}$	V_{DS}=V_{GS}, I_D=-250µA	-1.2	-1.7	-2.2	
Zero gate voltage drain current	I_{DSS}	V_{DS}=-32V, V_{GS}=0V, T_j=25°C	-	-0.08	-1	µA
		V_{DS}=-32V, V_{GS}=0V, T_j=125°C[2]	-	-20	-200	
Gate-source leakage current	I_{GSS}	V_{GS}=-16V, V_{DS}=0V	-	-	-100	nA
Drain-source on-state resistance	$R_{DS(on)}$	V_{GS}=-4.5V, I_D=-85A	-	5.1	6.6	mΩ
		V_{GS}=-10V, I_D=-90A	-	3.6	4.3	

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Dynamic characteristics[2]						
Input capacitance	C_{iss}	V_{GS}=0V, V_{DS}=-25V, f=1MHz	-	8900	11570	pF
Output capacitance	C_{oss}		-	2532	3800	
Reverse transfer capacitance	C_{rss}		-	100	200	
Turn-on delay time	$t_{d(on)}$	V_{DD}=-20V, V_{GS}=-10V, I_D=-90A, R_G=3.5Ω	-	20	-	ns
Rise time	t_r		-	20	-	
Turn-off delay time	$t_{d(off)}$		-	140	-	
Fall time	t_f		-	60	-	
Gate Charge Characteristics[2]						
Gate to source charge	Q_{gs}	V_{DD}=-32V, I_D=-90A, V_{GS}=0 to -10V	-	31	40	nC
Gate to drain charge	Q_{gd}		-	24	48	
Gate charge total	Q_g		-	135	176	
Gate plateau voltage	$V_{plateau}$		-	-3.5	-	V
Reverse Diode						
Diode continous forward current[2]	I_S	T_C=25°C	-	-	-90	A
Diode pulse current[2]	$I_{S,pulse}$		-	-	-360	
Diode forward voltage	V_{SD}	V_{GS}=0V, I_F=-90A, T_j=25°C	-	-1	-1.3	V
Reverse recovery time[2]	t_{rr}	V_R=-20V, I_F=-50A, di_F/dt=-100A/µs	-	63	-	ns
Reverse recovery charge[2]	Q_{rr}		-	72.3	-	nC

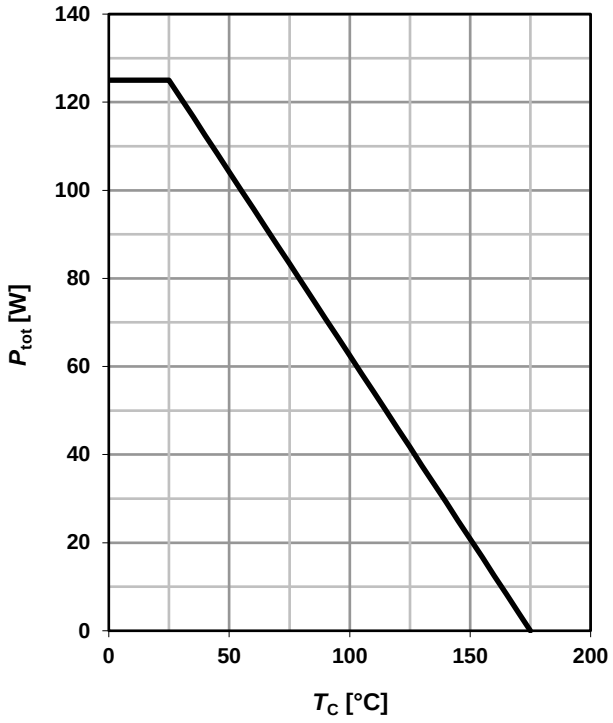
[1] Current is limited by bondwire; with an R_{thJC} = 1.2K/W the chip is able to carry -136A at 25°C.

[2] Defined by design. Not subject to production test.

[3] Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm^2 (one layer, 70 µm thick) copper area for drain connection. PCB is vertical in still air.

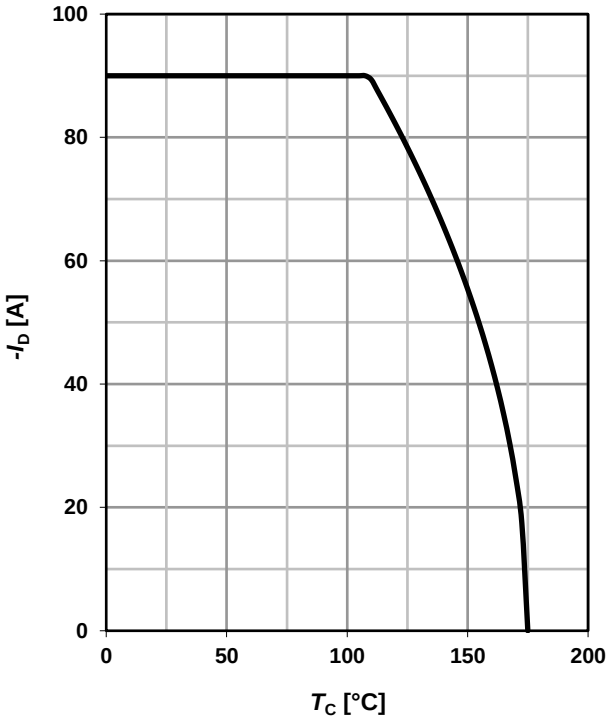
1 Power dissipation

$P_{tot} = f(T_C)$; $V_{GS} \leq -6V$



2 Drain current

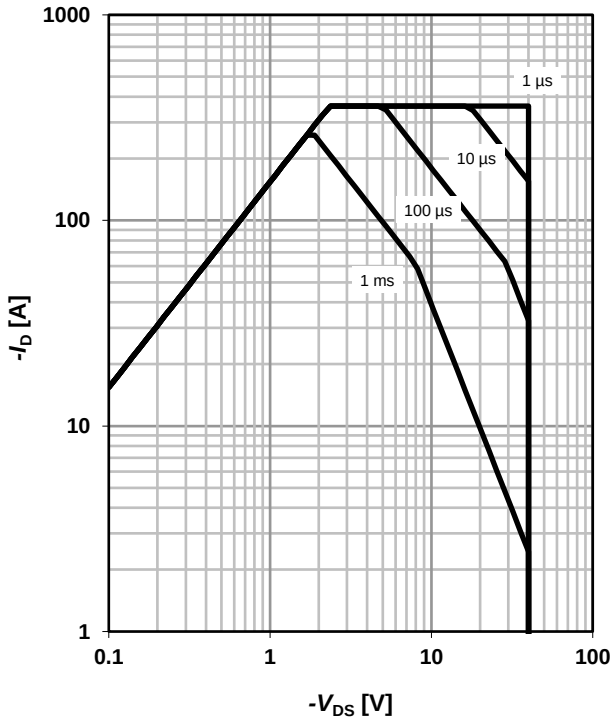
$I_D = f(T_C)$; $V_{GS} = -10V$



3 Safe operating area

$I_D = f(V_{DS})$; $T_C = 25$ °C; $D = 0$

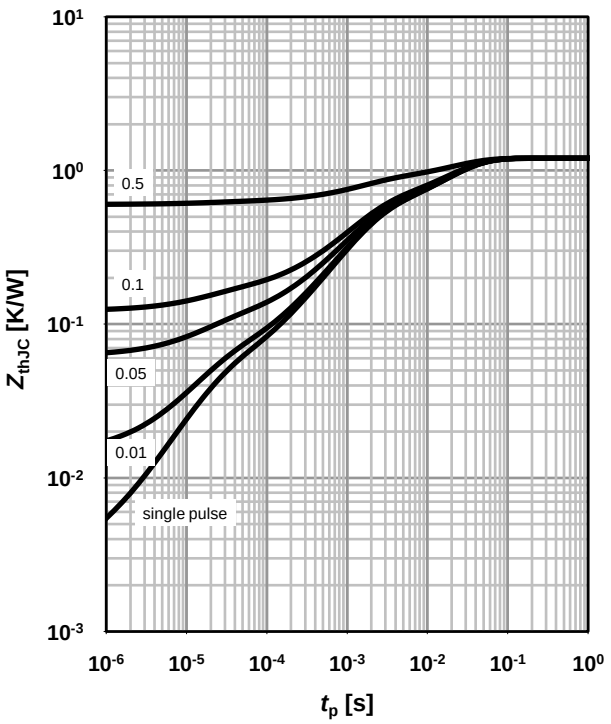
parameter: t_p



4 Max. transient thermal impedance

$Z_{thJC} = f(t_p)$

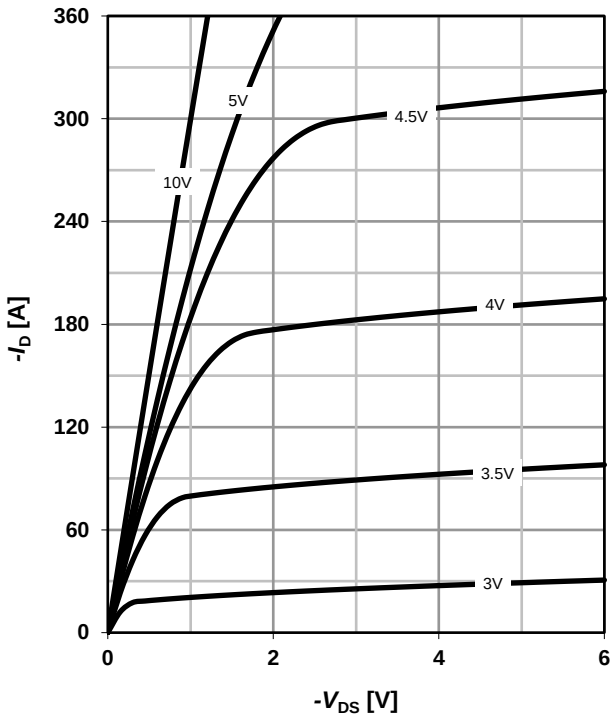
parameter: $D = t_p/T$



5 Typ. output characteristics

$I_D = f(V_{DS})$; $T_j = 25$ °C

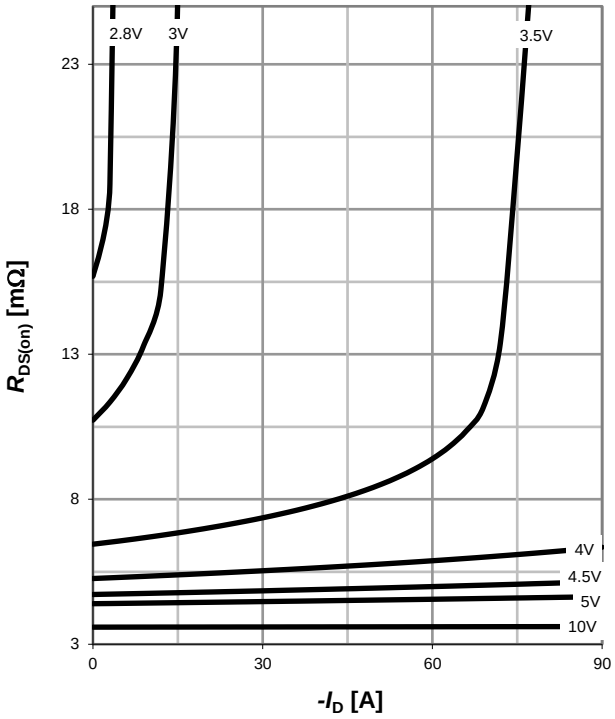
parameter: $-V_{GS}$



6 Typ. drain-source on-state resistance

$R_{DS(on)} = (I_D)$; $T_j = 25$ °C

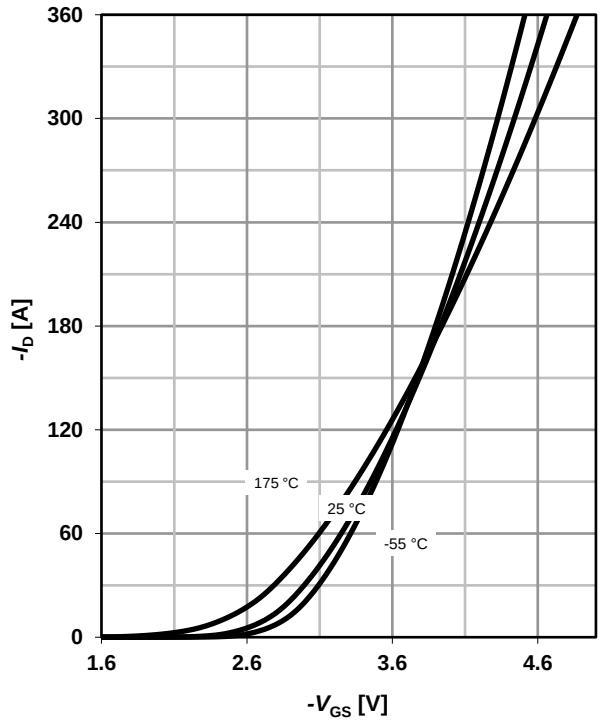
parameter: $-V_{GS}$



7 Typ. transfer characteristics

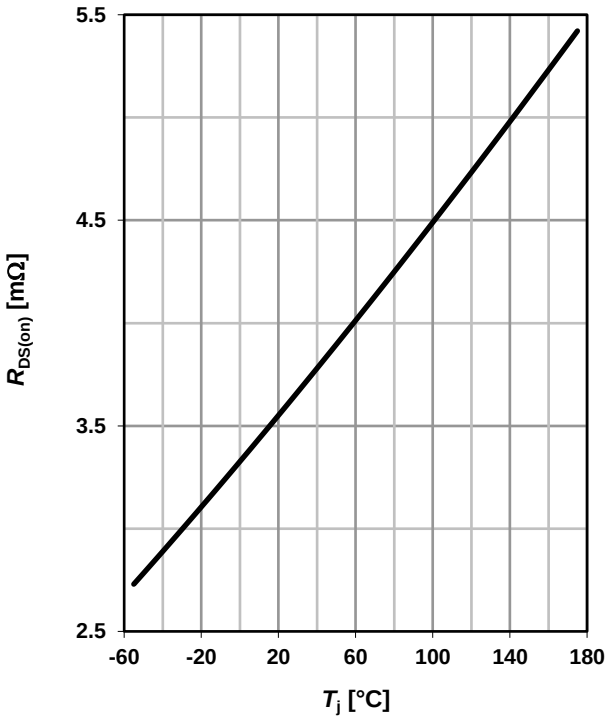
$I_D = f(V_{GS})$; $V_{DS} = -6$V

parameter: T_j



8 Typ. drain-source on-state resistance

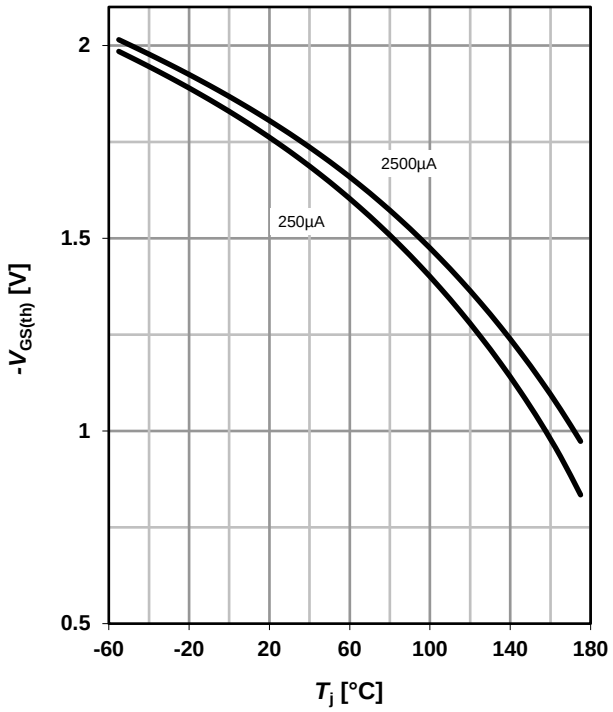
$R_{DS(on)} = f(T_j)$; $I_D = -90$ A; $V_{GS} = -10$ V



9 Typ. gate threshold voltage

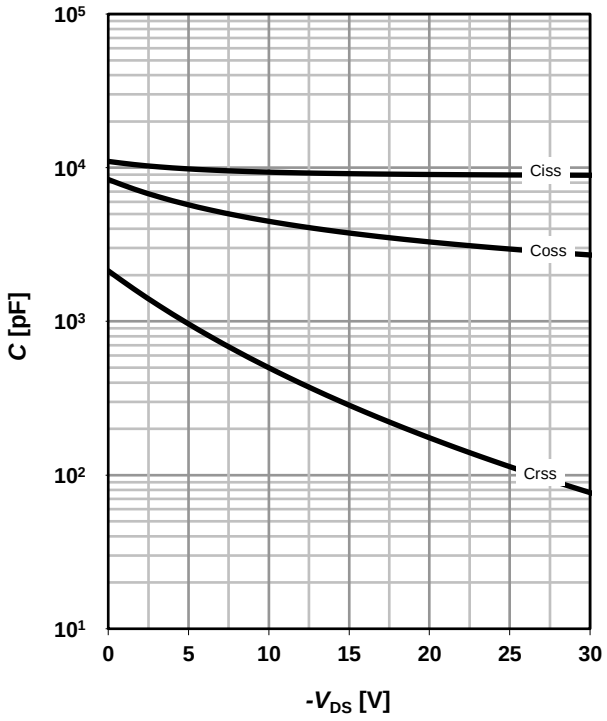
$V_{GS(th)} = f(T_j)$; $V_{GS} = V_{DS}$

parameter: $-I_D$



10 Typ. capacitances

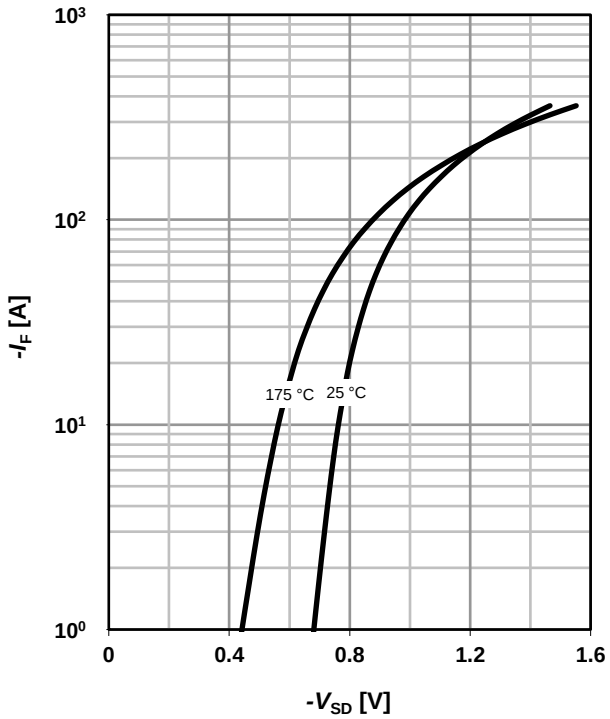
$C = f(V_{DS})$; $V_{GS} = 0$ V; $f = 1$ MHz



11 Typical forward diode characteristicis

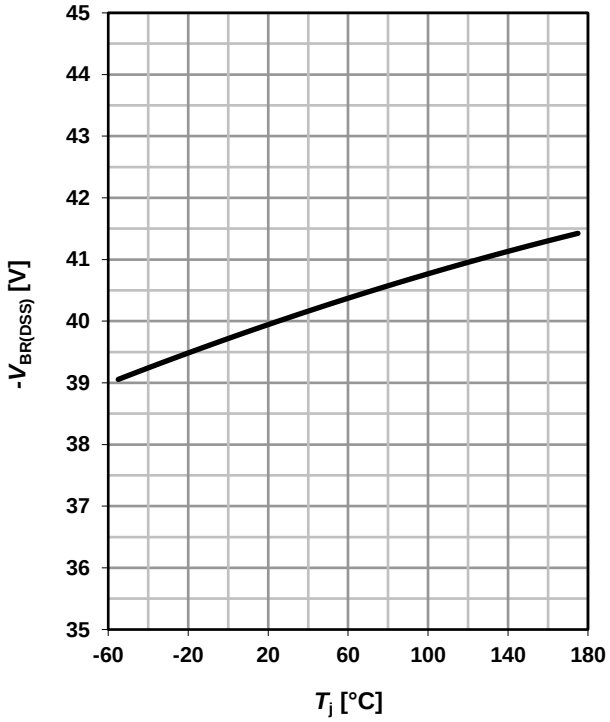
IF = f(V_{SD})

parameter: T_j



12 Drain-source breakdown voltage

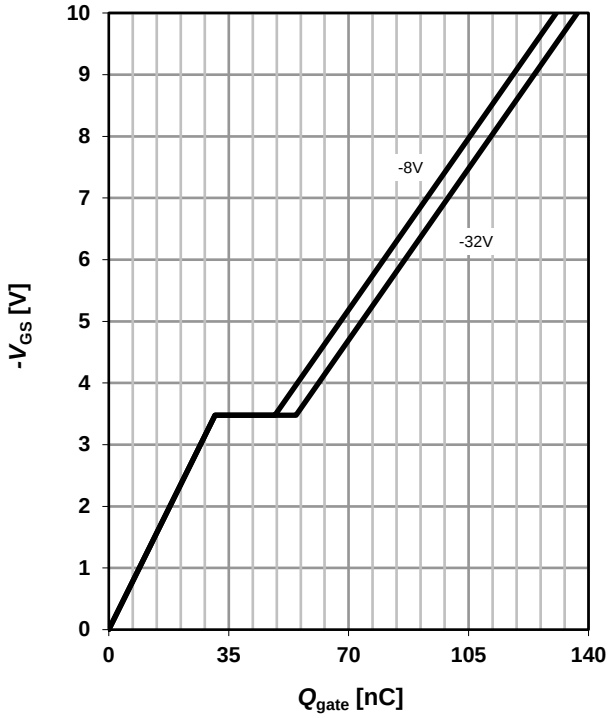
$V_{BR(DSS)} = f(T_j)$; $I_D = -1$ mA



13 Typ. gate charge

$V_{GS} = f(Q_{gate})$; I_D = -90 A pulsed

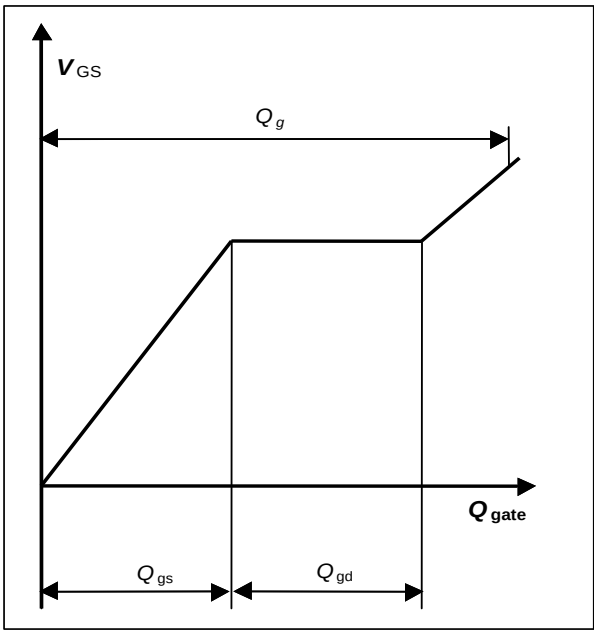
parameter: V_{DD}



14 Gate charge waveforms

$V_{GS} = f(Q_{gate})$; I_D = -90 A pulsed

parameter: V_{DD}



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Revision History

Version	Date	Changes
1.0	27.04.2011	Final Data Sheet
1.1	21.12.2012	Update of diagram 8
1.2	04.07.2019	V_{GS} changed